



PHYSIKALISCHES KOLLOQUIUM

Mittwoch, den 18.05.2011, um 17:15 Uhr

Ort: Reichenhainer Str. 90; Neues Hörsaalgebäude, Raum: 2/N013

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**Materials Chemistry
RWTH Aachen
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Growth of Oxide Thin Films: Atomic Playground

Molecular dynamics (MD) has been beneficial for unraveling physics of ion-surface processes on the atomic level in many systems. Here, the growth of RuO_2 and Al_2O_3 thin films is studied.

It is our ambition to identify suitable alloying elements for RuO_2 ($P4_2/mnm$), based on quantum mechanically guided design, which improve the transport properties and phase stability. Using *ab initio* calculations, we probe all 4d transition metals and identify Nb to be the best choice. Based on this design proposal, Nb alloyed RuO_2 thin films are grown by combinatorial reactive sputtering. Nb is incorporated in the rutile structure. Nanorods are formed and Nb_2O_5 coordination appears at Nb contents ≥ 2.9 at.%. This may be understood based on our *ab initio* MD data. Surface coarsening on the atomic scale occurs due to O crosslinking of two neighboring NbO_6 octahedra. Hence, it is reasonable to assume that NbO_6 octahedra contribute towards the experimentally observed formation of nanorods. A monoenergetic Al^+ beam generated by a filtered cathodic arc is employed for the deposition of Al_2O_3 films at well defined ion energies. Structural analysis shows that Al^+ energies of 40 eV or larger favor the formation of the thermodynamically stable $\alpha\text{-Al}_2\text{O}_3$ phase ($R\bar{3}c$) at the expense of metastable Al_2O_3 ($Fd\bar{3}m$). These Al bombardment induced structural changes in $\alpha\text{-Al}_2\text{O}_3$ and $\gamma\text{-Al}_2\text{O}_3$ were studied using *ab initio* MD. Diffusion and irradiation damage occur for both polymorphs in the kinetic energy range from 3.5 to 40 eV. However, for $\gamma\text{-Al}_2\text{O}_3(001)$ subplantation of impinging Al causes significantly larger irradiation damage and hence larger mobility as compared to $\alpha\text{-Al}_2\text{O}_3$. Consequently, fast diffusion along $\gamma\text{-Al}_2\text{O}_3(001)$ gives rise to preferential $\alpha\text{-Al}_2\text{O}_3(0001)$ growth, which is consistent with our structure evolution experiments.

Alle Zuhörer sind ab 17:00 Uhr zum Kaffee vor dem Hörsaal eingeladen.